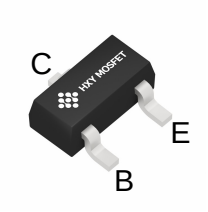
MMS8050-H-TP

NPN Plastic-Encapsulate Transistors

Features

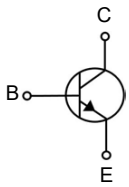
- Collector Current: I_C=0.5A
- Power Dissipation of 300mW



SOT-23

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MMS8050-H-TP	SOT-23	J3	3000



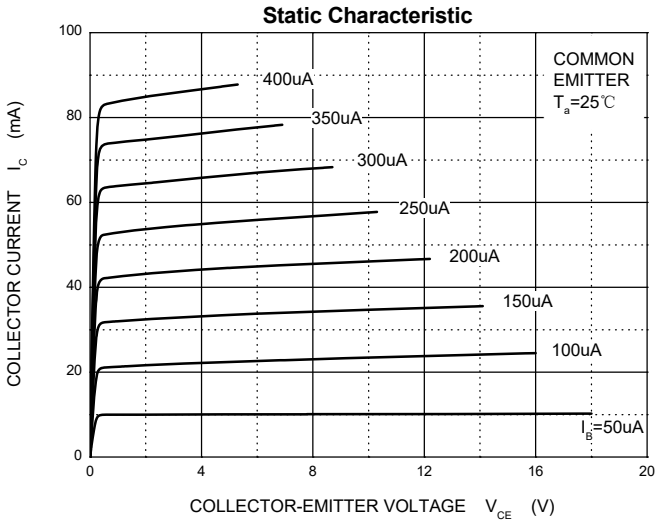
Maximum Ratings (Ta=25°C unless otherwise noted)

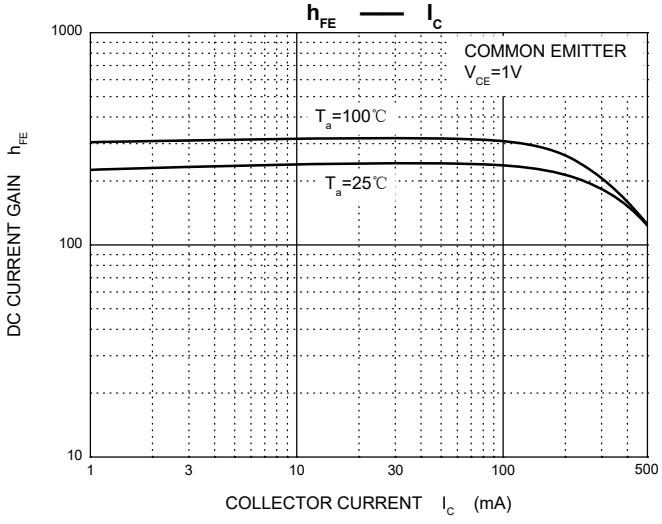
Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_C	350	mW
Thermal Resistance From Junction To Ambient	$R_{\Theta JA}$	416	℃/W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55～+150	℃

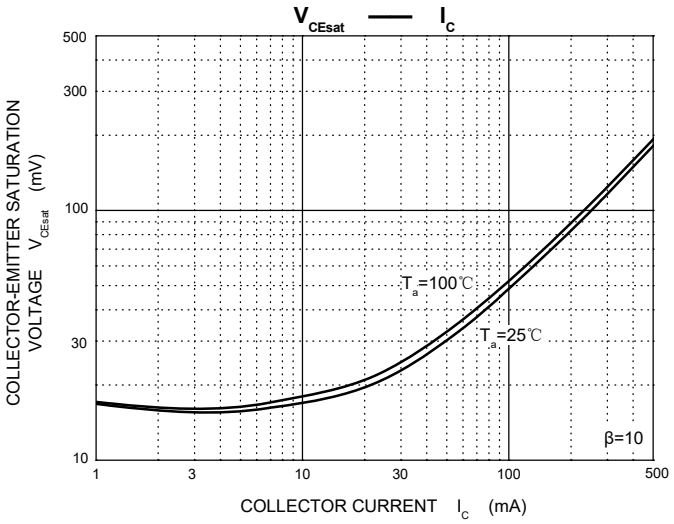
Electrical Characteristics (T_a=25°C unless otherwise specified)

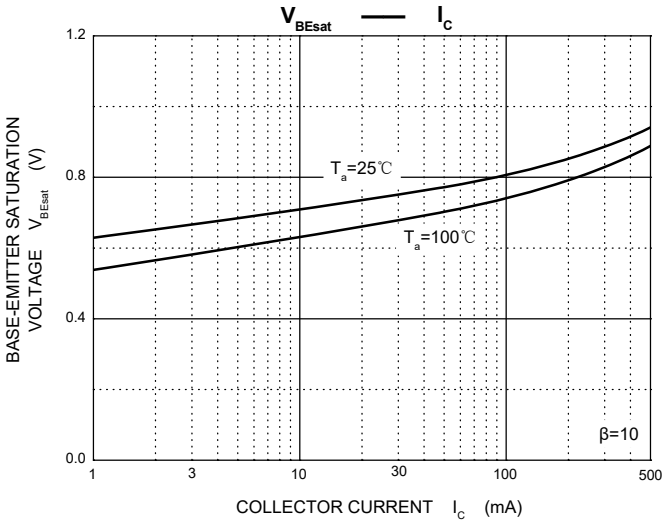
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=0.1mA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B= 0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	uA
Collector cut-off current	I_{CEO}	V_{CE}=20V, I_B=0			0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	uA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C=50mA	120		400	
	$h_{FE(2)}$	V_{CE}=1V, I_C=500mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=500mA, I_B=50mA			1.2	V
Base-emitter voltage	V_{BE}	V_{CB}=1V,I_C=10mA,			0.7	V
Transition frequency	f_T	V_{CE}=6V,I_C=20mA, f=30MHz	150			MHz
Collector output capacitance	C_{ob}	V_{CB}=6V, I_E=0, f=1MHz			8	pF

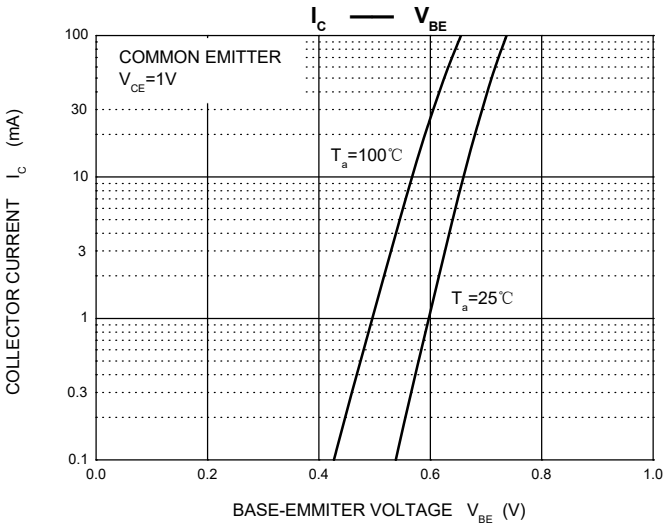
Typical Characteristics

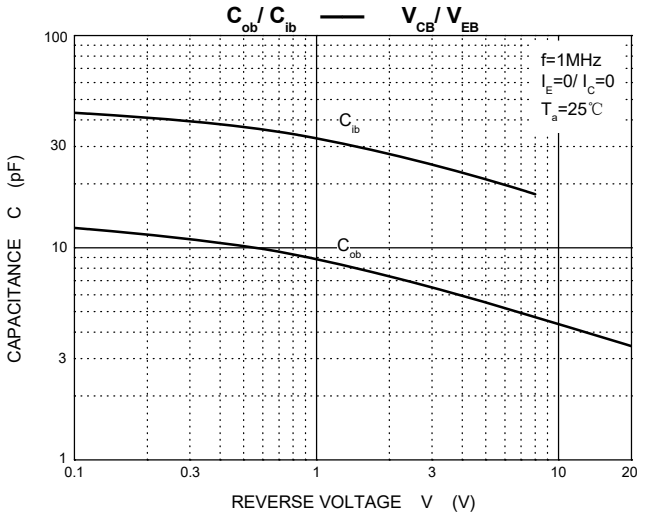


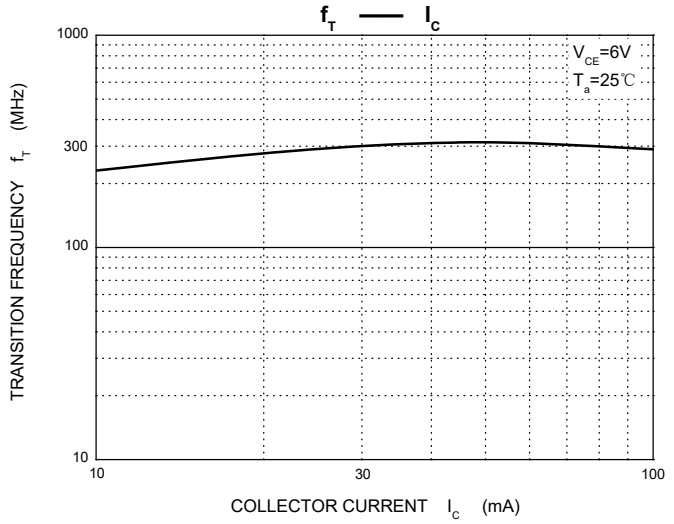


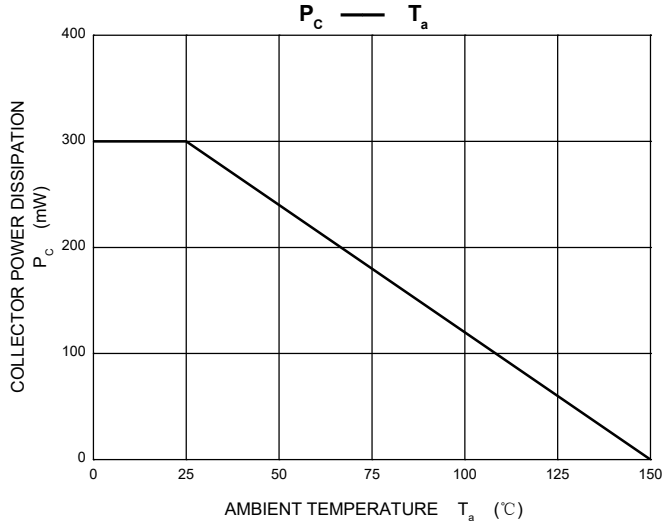

V_{CEsat} — I_C
COLLECTOR-EMITTER SATURATION VOLTAGE V_{CEsat} (mV)
500
300
100
30
10
1
3
10
30
100
500
T_a=100℃
T_a=25℃
β=10
COLLECTOR CURRENT I_C (mA)


V_{BEsat} — I_C
BASE-EMITTER SATURATION VOLTAGE V_{BEsat} (V)
1.2
0.8
0.4
0.0
1
3
10
30
100
500
T_a=25℃
T_a=100℃
β=10
COLLECTOR CURRENT I_C (mA)

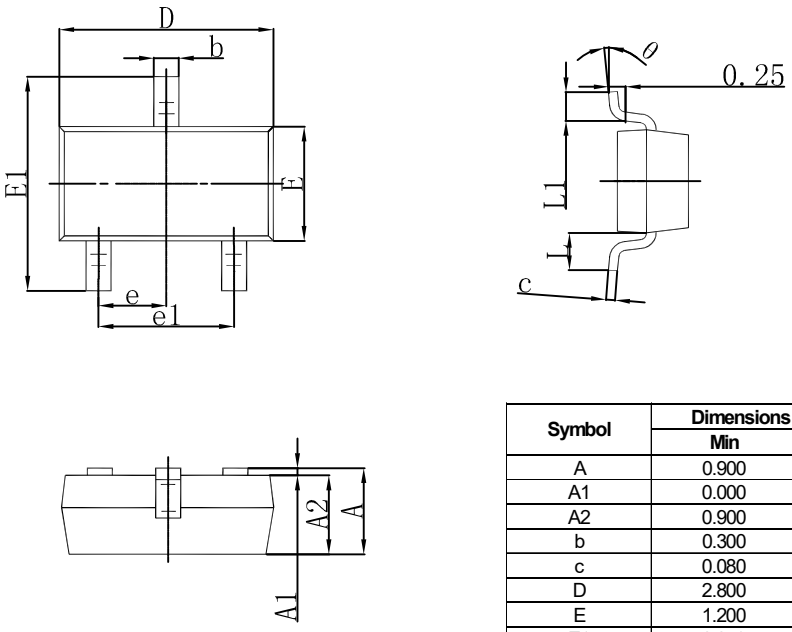

I_C — V_{BE}
COLLECTOR CURRENT I_C (mA)
100
30
10
3
1
0.3
0.1
COMMON EMITTER
V_{CE}=1V
T_a=100℃
T_a=25℃
0.0
0.2
0.4
0.6
0.8
1.0
BASE-EMMITER VOLTAGE V_{BE} (V)


C_{ob} / C_{ib} — V_{CB} / V_{EB}
CAPACITANCE C (pF)
100
30
10
3
1
f=1MHz
I_E=0/ I_C=0
T_a=25℃
C_{ib}
C_{ob}
0.1
0.3
1
3
10
20
REVERSE VOLTAGE V (V)


f_T — I_C
TRANSITION FREQUENCY f_T (MHz)
1000
300
100
10
V_{CE}=6V
T_a=25℃
10
30
100
COLLECTOR CURRENT I_C (mA)

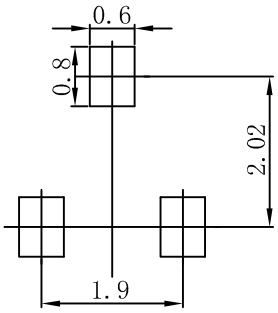

P_C — T_a
COLLECTOR POWER DISSIPATION P_C (mW)
400
300
200
100
0
0
25
50
75
100
125
150
AMBIENT TEMPERATURE T_a (℃)

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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